







SN74AHC1G09-Q1 SCLS927A - MAY 2023 - REVISED OCTOBER 2023

# SN74AHC1G09-Q1 Automotive Single 2–Input Positive-AND Gate With Open-Drain Output

## 1 Features

Texas

INSTRUMENTS

- AEC-Q100 Qualified for automotive applications: - Device temperature grade 1:
  - -40°C to +125°C, T<sub>A</sub>
  - Device HBM ESD Classification Level 2 Device CDM ESD Classification Level C6
- Operating range from 2 V to 5.5 V
- Low power consumption, 10-µA maximum I<sub>CC</sub> •
- Maximum t<sub>pd</sub> of 6 ns at 5 V
- ±8-mA output drive at 5 V
- Latch-up performance exceeds 250 mA per JESD 17

## 2 Applications

- Combining power good signals
- Enable digital signals

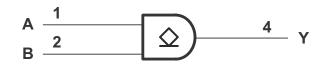
## **3 Description**

The SN74AHC1G09-Q1 is a single 2-input positive-AND gate with an open drain output configuration. The device performs the Boolean logic  $Y = A \times B$  in positive logic.

#### **Package Information**

PART NUMBER	PACKAGE <sup>(1)</sup>	PACKAGE SIZE <sup>(2)</sup>	BODY SIZE (NOM) <sup>(3)</sup>
SN74AHC1G09-Q1	DBV (SOT-23, 5)	2.9 mm × 2.8 mm	2.9 mm × 1.6 mm
31174ATIC 1803-QT	DCK (SC70, 5)	2 mm × 2.1 mm	2 mm × 1.25 mm

- (1) For all available packages, see the orderable addendum at the end of the data sheet.
- (2) The package size (length × width) is a nominal value and includes pins, where applicable.
- (3) The body size (length × width) is a nominal value and does not include pins.



Logic Diagram





## **Table of Contents**

1 Features	1
2 Applications	1
3 Description	1
4 Revision History	2
5 Pin Configuration and Functions	3
6 Specifications	4
6.1 Absolute Maximum Ratings	
6.2 ESD Ratings	
6.3 Recommended Operating Conditions	4
6.4 Thermal Information	5
6.5 Electrical Characteristics	5
6.6 Switching Characteristics, V <sub>CC</sub> = 3.3 V ± 0.3 V	5
6.7 Switching Characteristics, V <sub>CC</sub> = 5 V ± 0.5 V	5
6.8 Operating Characteristics	. 5
6.9 Typical Characteristics	6
7 Parameter Measurement Information	7
8 Detailed Description	8
8.1 Overview	8

8.2 Functional Block Diagram	8
8.3 Feature Description.	
8.4 Device Functional Modes	
9 Application and Implementation	9
9.1 Application Information	9
9.2 Typical Application	
9.3 Power Supply Recommendations	.10
9.4 Layout	. 10
10 Device and Documentation Support	.11
10.1 Documentation Support	. 11
10.2 Receiving Notification of Documentation Updates.	. 11
10.3 Support Resources	. 11
10.4 Trademarks	. 11
10.5 Electrostatic Discharge Caution	. 11
10.6 Glossary	. 11
11 Mechanical, Packaging, and Orderable	
Information	. 11

## **4** Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Cł	nanges from Revision * (May 2023) to Revision A (October 2023)	Page
•	Added the DBV package information throughout the data sheet	1



## **5** Pin Configuration and Functions

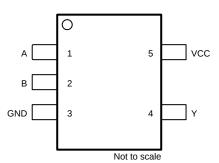


Figure 5-1. DBV or DCK Package, 5-Pin SOT-23 or SC70 (Top View)

#### Table 5-1. Pin Functions

PIN		TYPE <sup>(1)</sup>	DESCRIPTION					
NAME	NO.		DESCRIPTION					
A	1	I	Input					
В	2	I	Input					
GND	3		Ground					
V <sub>CC</sub>	5		Power pin					
Y	4	0	Output					

(1) I = input, O = output



## 6 Specifications 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage	-0.5	7	V
VI	Input voltage <sup>(2)</sup>	-0.5	7	V
Vo	Output voltage <sup>(2)</sup>	-0.5	V <sub>CC</sub> + 0.7	V
I <sub>IK</sub>	Input clamp current (V <sub>I</sub> < 0)	-20		mA
I <sub>OK</sub>	Output clamp current ( $V_0 < 0$ or $V_0 > V_{CC}$ )	-20		mA
lo	Continuous output current ( $V_O = 0$ to $V_{CC}$ )	-25	+25	mA
	Continuous current through V <sub>CC</sub> or GND	-50	+50	mA
TJ	Maximum junction temperature		150	°C
T <sub>stg</sub>	Storage temperature	-65	150	°C

(1) Operation outside the Absolute Maximum Rating may cause permanent device damage. Absolute Maximum Rating do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Condition. If used outside the Recommended Operating Condition but within the Absolute Maximum Rating, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

### 6.2 ESD Ratings

			VALUE	UNIT	
V	Electrostatic	Human body model (HBM), per AEC Q100-002 HBM ESD Classification Level 2 <sup>(1)</sup>	±2000	V	
V <sub>(ESD)</sub>	discharge	Charged device model (CDM), per AEC Q100-011 CDM ESD Classification Level C4B	±1000	v	

(1) AEC Q100-002 indicate that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

## 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted) <sup>(1)</sup>

			MIN	MAX	UNIT
V <sub>cc</sub>	Supply voltage		2	5.5	V
		V <sub>CC</sub> = 2 V	1.5		
VIH	High-level input voltage	V <sub>CC</sub> = 3 V	2.1		V
		V <sub>CC</sub> = 5.5 V	3.85		
		V <sub>CC</sub> = 2 V		0.5	
V <sub>IL</sub> Low-level input voltage	Low-level input voltage	V <sub>CC</sub> = 3 V		0.9	V
		V <sub>CC</sub> = 5.5 V		1.65	
VI	Input voltage		0	5.5	V
Vo	Output voltage		0	5.5	V
		V <sub>CC</sub> = 2 V		50	μA
I <sub>OL</sub>	Low-level output current	V <sub>CC</sub> = 3.3 V ± 0.3 V		4	
		V <sub>CC</sub> = 5 V ± 0.5 V		8	- mA
A+/A>/	Input transition rise or fall rate	V <sub>CC</sub> = 3.3 V ± 0.3 V		100	<b>n</b> o\/
Δt/Δv	Input transition rise or fall rate	V <sub>CC</sub> = 5 V ± 0.5 V		20	ns/V
T <sub>A</sub>	Operating free-air temperature		-40	125	°C

 All unused inputs of the device must be held at V<sub>CC</sub> or GND for proper device operation. See *Implications of Slow or Floating CMOS* Inputs, SCBA004.



## 6.4 Thermal Information

		SN74AHC	SN74AHC1G09-Q1			
	THERMAL METRIC <sup>(1)</sup>	DCK (SC70)	DBV (SOT-23)	UNIT		
		5 PINS	5 PINS			
R <sub>0JA</sub>	Junction-to-ambient thermal resistance	293.4	278.0	°C/W		
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	208.8	180.5	°C/W		
R <sub>θJB</sub>	Junction-to-board thermal resistance	180.6	184.4	°C/W		
Ψ <sub>JT</sub>	Junction-to-top characterization parameter	120.6	115.4	°C/W		
Ψ <sub>JB</sub>	Junction-to-board characterization parameter	179.5	183.4	°C/W		
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W		

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

### **6.5 Electrical Characteristics**

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V <sub>cc</sub>	T <sub>A</sub> = 25°C			T <sub>A</sub> = -40°C to	UNIT	
	TEST CONDITIONS	VCC	MIN	TYP	MAX	MIN TYP	MAX	UNIT
	I <sub>OL</sub> = 50 μA	2 V to 5 V			0.1		0.1	
V <sub>OL</sub>	I <sub>OL</sub> = 4 mA	3 V			0.36		0.55	V
	I <sub>OL</sub> = 8 mA	4.5 V			0.36		0.55	
I <sub>I</sub>	V <sub>1</sub> = 5.5 V or GND	0 V to 5.5 V			±0.1		±2	μA
I <sub>CC</sub>	$V_{I} = V_{CC}$ or GND, $I_{O} = 0$	5.5 V			1		20	μA
Ci	V <sub>I</sub> = V <sub>CC</sub> or GND	5 V		4	10		10	pF

## 6.6 Switching Characteristics, V<sub>CC</sub> = 3.3 V ± 0.3 V

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 7-1)

PARAMETER	FROM	TO (OUTPUT)	OUTPUT CAPACITANCE	T <sub>A</sub> = 25°C			T <sub>A</sub> = -40°C to +125°C			UNIT
PARAMETER	(INPUT)			MIN	TYP	MAX	MIN	TYP	MAX	
+	A or B	v	C <sub>L</sub> = 15 pF		3.6	7	1		8	ns
<sup>L</sup> PD	AUB	T	C <sub>L</sub> = 50 pF		6.5	11	1.5		12.5	ns

## 6.7 Switching Characteristics, $V_{CC}$ = 5 V ± 0.5 V

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 7-1)

PARAMETER	FROM	то	OUTPUT	T <sub>A</sub> = 25°C			T <sub>A</sub> = -40°C to +125°C			UNIT
FARAIVIETER	(INPUT)	(OUTPUT)	CAPACITANCE	MIN	TYP	MAX	MIN	TYP	MAX	
t	A or B	v	C <sub>L</sub> = 15 pF		2.5	5	1		6.5	ns
t <sub>PD</sub>	AOID	I	C <sub>L</sub> = 50 pF		4.6	7.5	1.5		8.5	ns

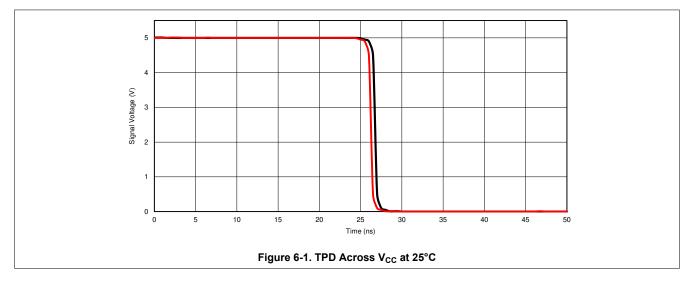
## 6.8 Operating Characteristics

V<sub>CC</sub> = 5 V, T<sub>A</sub> = 25°C

PARAMETER		TEST CONDITIONS	ТҮР	UNIT
C <sub>pd</sub>	Power dissipation capacitance	No load, f = 1 MHz	5	pF

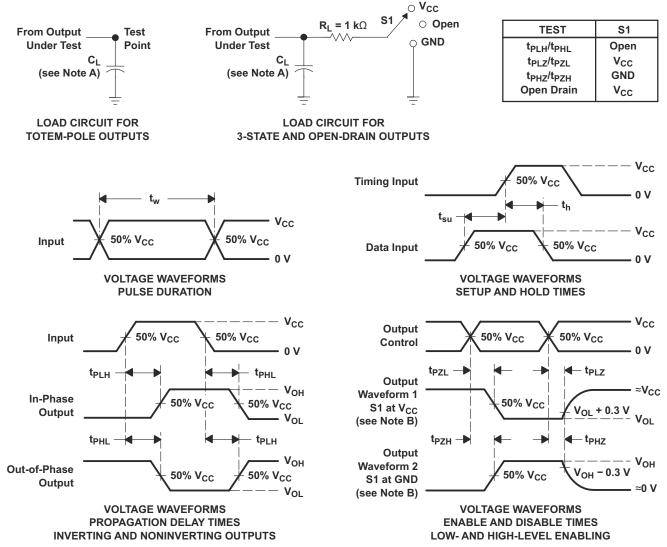


## 6.9 Typical Characteristics





## 7 Parameter Measurement Information



- A. C<sub>L</sub> includes probe and jig capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  1 MHz, Z<sub>O</sub> = 50  $\Omega$ , t<sub>r</sub>  $\leq$  3 ns, t<sub>f</sub>  $\leq$  3 ns.
- D. The outputs are measured one at a time with one input transition per measurement.
- E. All parameters and waveforms are not applicable to all devices.
- F. Since this device has open-drain outputs,  $t_{PLZ}$  and  $t_{PZL}$  are the same as  $t_{PD}$ .
- G.  $t_{PZL}$  is measured at V<sub>CC</sub>/2.
- H.  $t_{PLZ}$  is measured at V<sub>OL</sub> + 0.3 V.

#### Figure 7-1. Load Circuit and Voltage Waveforms

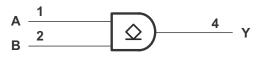


## 8 Detailed Description

## 8.1 Overview

The SN74AHC1G09-Q1 device contains one open-drain positive-AND gate with a maximum sink current of 8 mA. A wide operating range of 2 V to 5.5 V enables this device to be used in many different systems, and a low  $t_{pd}$  qualifies this device to be used in high-speed applications.

### 8.2 Functional Block Diagram



## 8.3 Feature Description

The wide operating voltage range of 2 V to 5 V allows the SN74AHC1G09-Q1 to be used in systems with many different voltage rails. In addition, the voltage tolerance on the output allows the device to be used for inverting up-translation or down-translation. The device is also equipped with Schmitt-trigger inputs, which increase the ability of the device to reject noise.

### 8.4 Device Functional Modes

Table 8-1 lists the functional modes of the SN74AHC1G09-Q1.

INP	OUTPUT			
Α	A B			
Н	Н	H(Z)		
L	Х	L		
Х	L	L		

#### Table 8-1. Function Table



## 9 Application and Implementation

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 9.1 Application Information

The SN74AHC1G09-Q1 is used in the following example in a basic power sequencing configuration. Power sequencing is often used in applications that require a processor or other delicate device with specific voltage timing requirements to protect the device from malfunctioning.

#### **9.2 Typical Application**

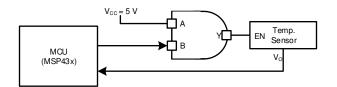


Figure 9-1. Typical Application Diagram

#### 9.2.1 Design Requirements

This device uses CMOS technology. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads, so routing and load conditions should be considered to prevent ringing.

#### 9.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions:
  - Rise time and fall time specifications. See ( $\Delta t/\Delta V$ ) in *Recommended Operating Conditions*.
  - Specified high and low levels. See (V<sub>IH</sub> and V<sub>IL</sub>) in *Recommended Operating Conditions*.
  - Inputs are overvoltage-tolerant, allowing them to go as high as (V<sub>I</sub> maximum) in *Recommended* Operating Conditions at any valid V<sub>CC</sub>.
- 2. Absolute Maximum Conditions:
  - Load currents should not exceed (I<sub>O</sub> maximum) per output and should not exceed (continuous current through V<sub>CC</sub> or GND) total current for the part. These limits are located in *Absolute Maximum Ratings*.
  - Outputs should not be pulled above V<sub>CC</sub>.



### 9.2.3 Application Curves

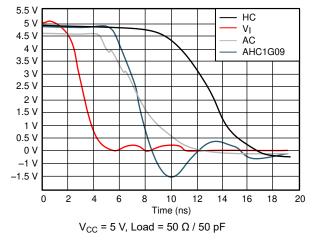


Figure 9-2. I<sub>CC</sub> vs Input Voltage

### 9.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in *Recommended Operating Conditions*.

Each V<sub>CC</sub> pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- $\mu$ F capacitor is recommended; if there are multiple V<sub>CC</sub> pins, then a 0.01- $\mu$ F or 0.022- $\mu$ F capacitor is recommended for each power pin. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1- $\mu$ F and 1- $\mu$ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

### 9.4 Layout

#### 9.4.1 Layout Guidelines

When using multiple bit logic devices, inputs must never float. In many cases, functions or parts of functions of digital logic devices are unused (for example, when only two inputs of a triple-input AND gate are used, or only 3 of the 4 buffer gates are used). Such input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states.

The following are the rules that must be observed under all circumstances:

- All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating.
- The logic level that should be applied to any particular unused input depends on the function of the device.
  Generally the unused inputs will be tied to GND or V<sub>CC</sub>, whichever makes more sense or is more convenient.

#### 9.4.2 Layout Example



Figure 9-3. Layout Diagram



## **10 Device and Documentation Support**

### **10.1 Documentation Support**

#### **10.1.1 Related Documentation**

For related documentation, see the following:

- Texas Instruments, Introduction to Logic application report
- Texas Instruments, Implications of Slow or Floating CMOS Inputs application note

#### **10.2 Receiving Notification of Documentation Updates**

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### **10.3 Support Resources**

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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#### 10.4 Trademarks

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#### **10.5 Electrostatic Discharge Caution**



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 10.6 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

## 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.



## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74AHC1G09QDBVRQ1	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	38RH	Samples
SN74AHC1G09QDCKRQ1	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1P5	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN74AHC1G09-Q1 :

Catalog : SN74AHC1G09

NOTE: Qualified Version Definitions:

Catalog - TI's standard catalog product



Texas

STRUMENTS

## TAPE AND REEL INFORMATION





#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	-	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AHC1G09QDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74AHC1G09QDCKRQ1	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3



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# PACKAGE MATERIALS INFORMATION

4-Nov-2023



\*All dimensions are nominal

Device Package Type		Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
SN74AHC1G09QDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0	
SN74AHC1G09QDCKRQ1	SC70	DCK	5	3000	190.0	190.0	30.0	

# **DBV0005A**



# **PACKAGE OUTLINE**

## SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
   This drawing is subject to change without notice.
   Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.



# DBV0005A

# **EXAMPLE BOARD LAYOUT**

## SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# DBV0005A

# **EXAMPLE STENCIL DESIGN**

## SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



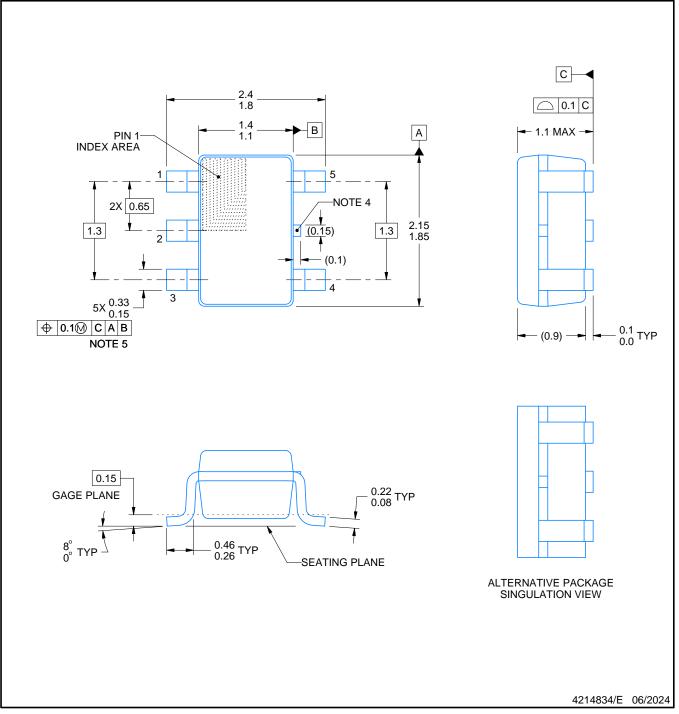
# **DCK0005A**



# **PACKAGE OUTLINE**

## SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
   This drawing is subject to change without notice.
   Reference JEDEC MO-203.

- 4. Support pin may differ or may not be present.
- 5. Lead width does not comply with JEDEC.
- 6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side



# **DCK0005A**

# **EXAMPLE BOARD LAYOUT**

## SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

Publication IPC-7351 may have alternate designs.
 Solder mask tolerances between and around signal pads can vary based on board fabrication site.

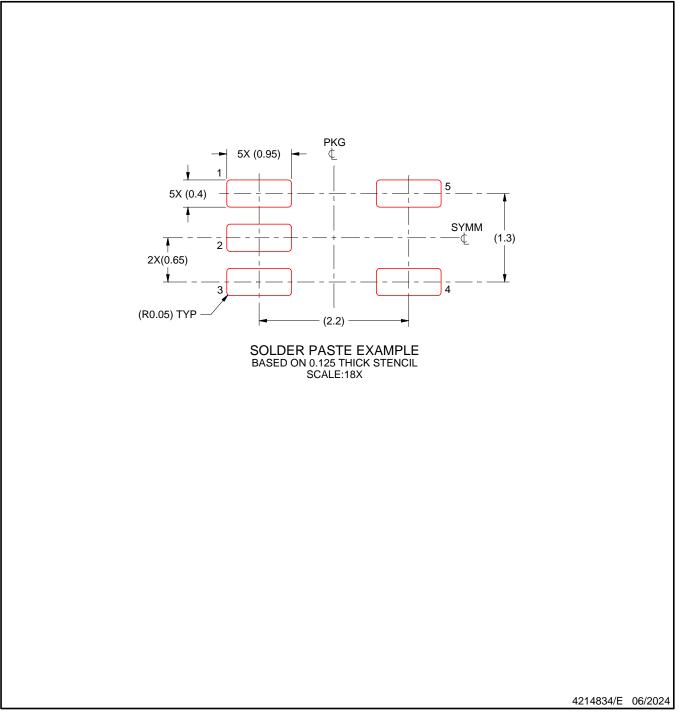


# DCK0005A

# **EXAMPLE STENCIL DESIGN**

## SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

10. Board assembly site may have different recommendations for stencil design.



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